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# PDTB123E series

PNP 500 mA, 50 V resistor-equipped transistors; R1 = 2.2 k $\Omega$ , R2 = 2.2 k $\Omega$ 

Rev. 02 — 16 November 2009

Product data sheet

### 1. Product profile

### 1.1 General description

500 mA PNP Resistor-Equipped Transistors (RET) family.

Table 1. Product overview

| Type number  | Package |        | NPN complement |           |
|--------------|---------|--------|----------------|-----------|
|              | NXP     | JEITA  | JEDEC          |           |
| PDTB123EK    | SOT346  | SC-59A | TO-236         | PDTD123EK |
| PDTB123ES[1] | SOT54   | SC-43A | TO-92          | PDTD123ES |
| PDTB123ET    | SOT23   | -      | TO-236AB       | PDTD123ET |

<sup>[1]</sup> Also available in SOT54A and SOT54 variant packages (see Section 2).

### 1.2 Features

- Built-in bias resistors
- Simplifies circuit design
- 500 mA output current capability
- Reduces component count
- Reduces pick and place costs
- ±10 % resistor ratio tolerance

### 1.3 Applications

- Digital application in automotive and industrial segments
- Controlling IC inputs

- Cost-saving alternative for BC807 series in digital applications
- Switching loads

### 1.4 Quick reference data

Table 2. Quick reference data

| Symbol         | Parameter                 | Conditions | Min  | Тур | Max  | Unit |
|----------------|---------------------------|------------|------|-----|------|------|
| $V_{CEO}$      | collector-emitter voltage | open base  | -    | -   | -50  | V    |
| I <sub>O</sub> | output current (DC)       |            | -    | -   | -500 | mA   |
| R1             | bias resistor 1 (input)   |            | 1.54 | 2.2 | 2.86 | kΩ   |
| R2/R1          | bias resistor ratio       |            | 0.9  | 1.0 | 1.1  |      |



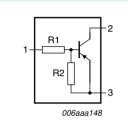
## 2. Pinning information

Table 3. Pinning

| Pin   | Description        | Simplified outline | Symbol |
|-------|--------------------|--------------------|--------|
| SOT54 |                    |                    |        |
| 1     | input (base)       |                    |        |
| 2     | output (collector) |                    | R1 1 2 |
| 3     | GND (emitter)      | 001aab347          | 1 R2 3 |

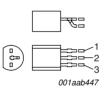
| S | $\cap$ | т | _ | л | ٨ |
|---|--------|---|---|---|---|
| 3 | v      |   | ວ | 4 | н |

| 1 | input (base)       |  |
|---|--------------------|--|
| 2 | output (collector) |  |
| 3 | GND (emitter)      |  |

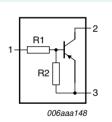


#### **SOT54** variant

| 1 | input (base)       |
|---|--------------------|
| 2 | output (collector) |
| 3 | GND (emitter)      |

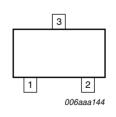


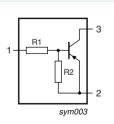
001aab348



### **SOT23, SOT346**

| 1 | input (base)       |
|---|--------------------|
| 2 | GND (emitter)      |
| 3 | output (collector) |





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### 3. Ordering information

Table 4. Ordering information

| Type number  | Package |   |         |  |  |  |
|--------------|---------|---|---------|--|--|--|
|              | Name    | Description   | Version |  |  |  |
| PDTB123EK    | SC-59A  | plastic surface mounted package; 3 leads                    | SOT346  |  |  |  |
| PDTB123ES[1] | SC-43A  | plastic single-ended leaded (through hole) package; 3 leads | SOT54   |  |  |  |
| PDTB123ET    | -       | plastic surface mounted package; 3 leads                    | SOT23   |  |  |  |

<sup>[1]</sup> Also available in SOT54A and SOT54 variant packages (see Section 2 and Section 9).

### 4. Marking

Table 5. Marking codes

| Type number | Marking code <sup>[1]</sup> |
|-------------|-----------------------------|
| PDTB123EK   | E2                          |
| PDTB123ES   | B123ES                      |
| PDTB123ET   | *7S                         |

<sup>[1] \* = -:</sup> made in Hong Kong

### 5. Limiting values

Table 6. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

| Symbol           | Parameter                 | Conditions                  | Min          | Max  | Unit |
|------------------|---------------------------|-----------------------------|--------------|------|------|
| $V_{CBO}$        | collector-base voltage    | open emitter                | -            | -50  | V    |
| V <sub>CEO</sub> | collector-emitter voltage | open base                   | -            | -50  | V    |
| $V_{EBO}$        | emitter-base voltage      | open collector              | -            | -10  | V    |
| VI               | input voltage             |                             |              |      |      |
|                  | positive                  |                             | -            | +10  | V    |
|                  | negative                  |                             | -            | -12  | V    |
| I <sub>O</sub>   | output current (DC)       |                             | -            | -500 | mA   |
| P <sub>tot</sub> | total power dissipation   | $T_{amb} \le 25  ^{\circ}C$ |              |      |      |
|                  | SOT346                    |                             | <u>[1]</u> - | 250  | mW   |
|                  | SOT54                     |                             | <u>[1]</u> - | 500  | mW   |
|                  | SOT23                     |                             | <u>[1]</u> - | 250  | mW   |
| T <sub>stg</sub> | storage temperature       |                             | -65          | +150 | °C   |
| Tj               | junction temperature      |                             | -            | 150  | °C   |
| $T_{amb}$        | ambient temperature       |                             | -65          | +150 | °C   |

<sup>[1]</sup> Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.

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<sup>\* =</sup> p: made in Hong Kong

<sup>\* =</sup> t: made in Malaysia

<sup>\* =</sup> W: made in China

### 6. Thermal characteristics

Table 7. Thermal characteristics

| Symbol        | Parameter   | Conditions  | Min | Тур | Max | Unit |
|---------------|---|-------------|-----|-----|-----|------|
| $R_{th(j-a)}$ | thermal resistance<br>from junction to<br>ambient | in free air | Ш   |     |     |      |
|               | SOT346  |             | -   | -   | 500 | K/W  |
|               | SOT54   |             | -   | -   | 250 | K/W  |
|               | SOT23   |             | -   | -   | 500 | K/W  |
|               |   |             |     |     |     |      |

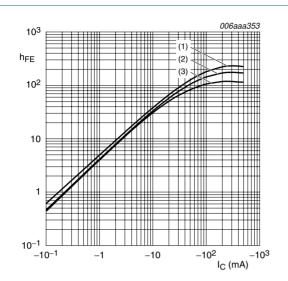
<sup>[1]</sup> Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

### 7. Characteristics

Table 8. Characteristics

T<sub>amb</sub> = 25 °C unless otherwise specified.

| Symbol              | Parameter                            | Conditions   | Min  | Тур  | Max  | Unit |
|---------------------|--------------------------------------|--|------|------|------|------|
| $I_{CBO}$           |                                      | $V_{CB} = -40 \text{ V}; I_E = 0 \text{ A}$                    | -    | -    | -100 | nA   |
|                     | current                              | $V_{CB} = -50 \text{ V}; I_E = 0 \text{ A}$                    | -    | -    | -100 | nA   |
| I <sub>CEO</sub>    | collector-emitter<br>cut-off current | $V_{CE} = -50 \text{ V}; I_B = 0 \text{ A}$                    | -    | -    | -0.5 | μΑ   |
| I <sub>EBO</sub>    | emitter-base cut-off current         | $V_{EB} = -5 \text{ V}; I_C = 0 \text{ A}$                     | -    | -    | -2.0 | mA   |
| h <sub>FE</sub>     | DC current gain                      | $V_{CE} = -5 \text{ V}; I_C = -50 \text{ mA}$                  | 40   | -    | -    |      |
| V <sub>CEsat</sub>  | collector-emitter saturation voltage | $I_C = -50 \text{ mA}; I_B = -2.5 \text{ mA}$                  | -    | -    | -0.3 | mV   |
| $V_{I(\text{off})}$ | off-state input voltage              | $V_{CE} = -5 \text{ V}; I_C = -100 \mu\text{A}$                | -0.6 | -1.1 | -1.8 | V    |
| $V_{I(on)}$         | on-state input<br>voltage            | $V_{CE} = -0.3 \text{ V};$ $I_{C} = -20 \text{ mA}$            | -1.0 | -1.5 | -2.0 | V    |
| R1                  | bias resistor 1 (input)              |  | 1.54 | 2.2  | 2.86 | kΩ   |
| R2/R1               | bias resistor ratio                  |  | 0.9  | 1.0  | 1.1  |      |
| C <sub>c</sub>      | collector capacitance                | $V_{CB} = -10 \text{ V}; I_E = I_e = 0 \text{ A};$ f = 100 MHz | -    | 11   | -    | pF   |



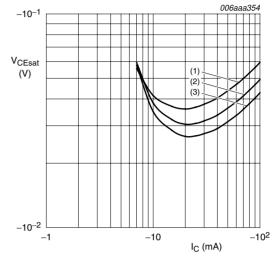
$$V_{CE} = -5 \text{ V}$$

(1) 
$$T_{amb} = 100 \, ^{\circ}C$$

(2) 
$$T_{amb} = 25 \, ^{\circ}C$$

(3) 
$$T_{amb} = -40 \, ^{\circ}C$$

Fig 1. DC current gain as a function of collector current; typical values



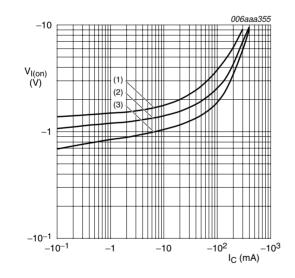
$$I_{C}/I_{B} = 20$$

(1) 
$$T_{amb} = 100 \, ^{\circ}C$$

(2) 
$$T_{amb} = 25 \, ^{\circ}C$$

(3) 
$$T_{amb} = -40 \, ^{\circ}C$$

Fig 2. Collector-emitter saturation voltage as a function of collector current; typical values



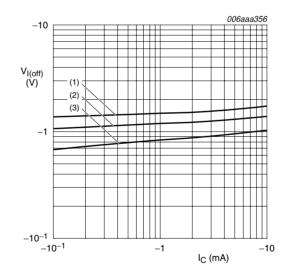
$$V_{CE} = -0.3 \text{ V}$$

(1) 
$$T_{amb} = -40 \, ^{\circ}C$$

(2) 
$$T_{amb} = 25 \, ^{\circ}C$$

(3) 
$$T_{amb} = 100 \, ^{\circ}C$$

Fig 3. On-state input voltage as a function of collector current; typical values



$$V_{CE} = -5 \text{ V}$$

(1) 
$$T_{amb} = -40 \, ^{\circ}C$$

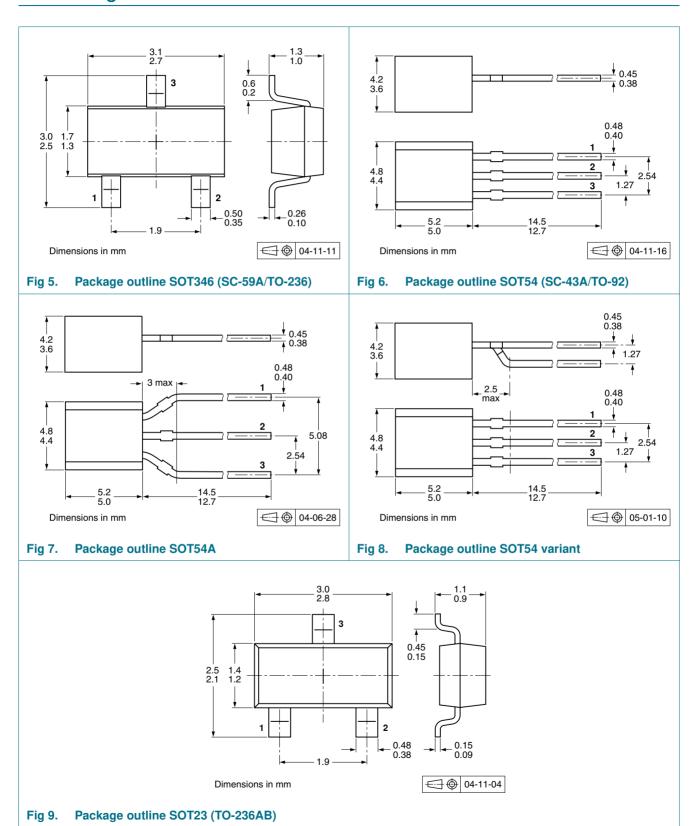
(2) 
$$T_{amb} = 25 \, ^{\circ}C$$

(3) 
$$T_{amb} = 100 \, ^{\circ}C$$

Fig 4. Off-state input voltage as a function of collector current; typical values

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### 8. Package outline



## 9. Packing information

Table 9. Packing methods

The indicated -xxx are the last three digits of the 12NC ordering code.[1]

| Type number | Package       | Description                    | Packing quantity |      |       |
|-------------|---------------|--------------------------------|------------------|------|-------|
|             |               |                                | 3000             | 5000 | 10000 |
| PDTB123EK   | SOT346        | 4 mm pitch, 8 mm tape and reel | -115             | -    | -135  |
| PDTB123ES   | SOT54         | bulk, straight leads           | -                | -412 | -     |
|             | SOT54A        | tape and reel, wide pitch      | -                | -    | -116  |
|             |               | tape ammopack, wide pitch      | -                | -    | -126  |
|             | SOT54 variant | bulk, delta pinning            | -                | -112 | -     |
| PDTB123ET   | SOT23         | 4 mm pitch, 8 mm tape and reel | -215             | -    | -235  |

<sup>[1]</sup> For further information and the availability of packing methods, see Section 12.



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PNP 500 mA resistor-equipped transistors; R1 = 2.2 k $\Omega$ , R2 = 2.2 k $\Omega$ 

## 10. Revision history

### Table 10. Revision history

|                | •   |                    |               |                |  |
|----------------|---|--------------------|---------------|----------------|--|
| Document ID    | Release date  | Data sheet status  | Change notice | Supersedes     |  |
| PDTB123E_SER_2 | 20091116  | Product data sheet | -             | PDTB123E_SER_1 |  |
| Modifications: | <ul> <li>This data sheet was changed to reflect the new company name NXP Semiconductors,<br/>including new legal definitions and disclaimers. No changes were made to the technical<br/>content.</li> </ul> |                    |               |                |  |
| PDTB123E_SER_1 | 20050427  | Product data sheet | -             | -              |  |

### 11. Legal information

#### 11.1 Data sheet status

| Document status[1][2]          | Product status[3] | Definition  |
|--------------------------------|-------------------|---|
| Objective [short] data sheet   | Development       | This document contains data from the objective specification for product development. |
| Preliminary [short] data sheet | Qualification     | This document contains data from the preliminary specification.                       |
| Product [short] data sheet     | Production        | This document contains the product specification.                                     |

- [1] Please consult the most recently issued document before initiating or completing a design.
- [2] The term 'short data sheet' is explained in section "Definitions"
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# PDTB123E series

### PNP 500 mA resistor-equipped transistors; R1 = 2.2 k $\Omega$ , R2 = 2.2 k $\Omega$

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